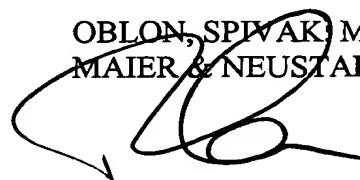


REMARKS

Applicants appreciate the indication that Claim 16 is allowable. By the above amendment, Applicant has accepted this allowable subject matter without prejudice or disclaimer. A Notice of Allowance is earnestly solicited.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,  
MAIER & NEUSTADT, P.C.



Richard L. Treanor, Ph.D.  
Attorney of Record  
Registration No. 36,379



**22850**

(703) 413-3000  
RLT/cja

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Amendment Filed: Herewith

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IN THE CLAIMS

- 1. (Amended) A semiconductor structure comprising:  
a monocrystalline substrate;  
an amorphous layer formed on the substrate; and  
a first monocrystalline nitride material layer overlying the amorphous layer and  
formed of at least one selected from the group [comprising] consisting of GaN, GaInN,  
AlGa<sub>0.5</sub>N, SiN and AlN, wherein the first monocrystalline nitride material layer is formed by  
nitridation of a first monocrystalline material layer selected from the group  
consisting of GaAs, GaInAs, AlGaAs, Si and AlAs, and wherein said first monocrystalline  
material layer has a thickness in the range of from about 20 angstroms to about 50 angstroms.
3. (Cancelled).  
16-42. (Cancelled).  
43. (New).--